

### ● General Description

The AGM30P10A combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

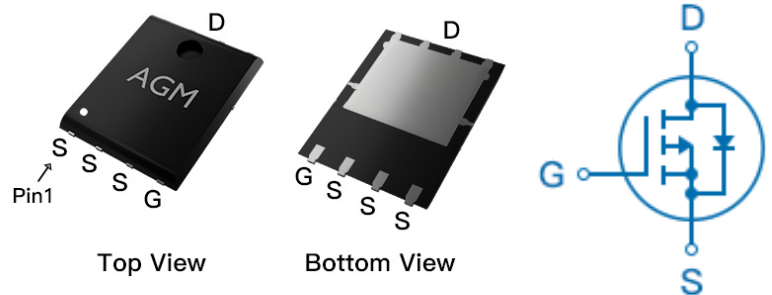
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
-30V	11mΩ	-40A

### PDFN5\*6 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P10A	AGM30P10A	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	-40	A
	Drain Current-Continuous(Tc=100°C)	-24	A
IDM (pluse)	Drain Current-Pulsed <b>(Note 2)</b>	-160	A
PD	Maximum Power Dissipation(Tc=25°C)	37	w
	Maximum Power Dissipation(Tc=100°C)	15	w
EAS	Avalanche energy <b>(Note 3)</b>	100	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	20	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	3.4	°C/W

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1.0	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	--	-2.2	V
gFS	Forward Transconductance	VDS=-5V,ID=-5A	--	11	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-10A	--	11	13.9	mΩ
		VGS=-4.5V, ID=-5A	--	16	23	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=-15V,VGS=0V F=1MHZ	--	1443	--	pF
Coss	Output Capacitance		--	191	--	pF
Crss	Reverse Transfer Capacitance		--	141	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	14	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-25V, RL=0.75Ω,RGEN=3.3Ω	--	13	--	nS
tr	Turn-on Rise Time		--	8.5	--	nS
td(off)	Turn-Off Delay Time		--	26	--	nS
tf	Turn-Off Fall Time		--	12	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-25V, ID=-8A	--	15	--	nC
Qgs	Gate-Source Charge		--	4.0	--	nC
Qgd	Gate-Drain Charge		--	6.0	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	-40	A
VSD	Forward on Voltage	VGS=0V,IS=-10A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-10A , di/dt=100A/μs , TJ=25°C	--	14	--	ns
Qrr	Reverse Recovery Charge		--	5.0	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C,VDD=-15V,Vgs=-10V,ID=-20A, L=0.5mH,RG= 25ohm

Fig.1 Power Dissipation Derating Curve

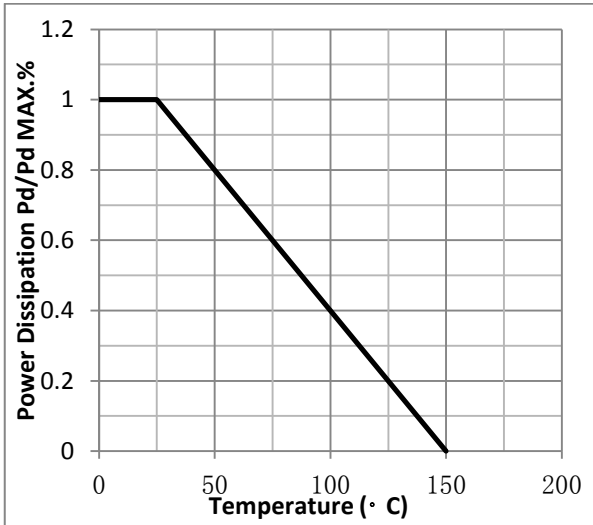


Fig.2 Typical output Characteristics

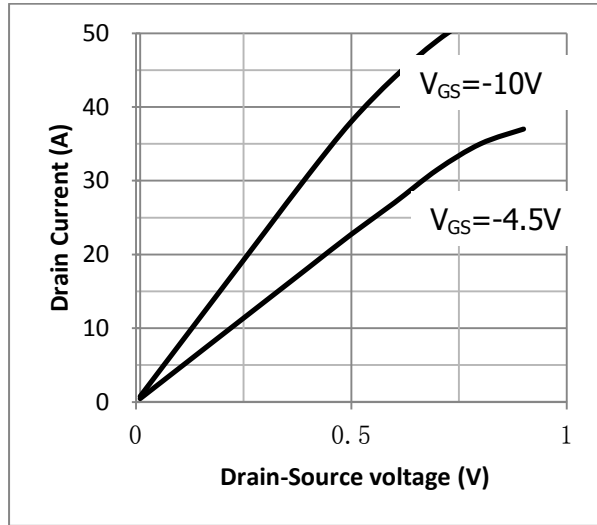


Fig.3 Threshold Voltage V.S Junction Temperature

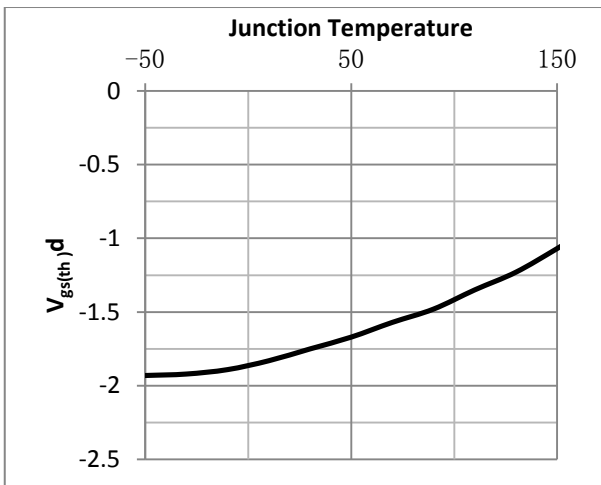


Fig.4 Resistance V.S Drain Current

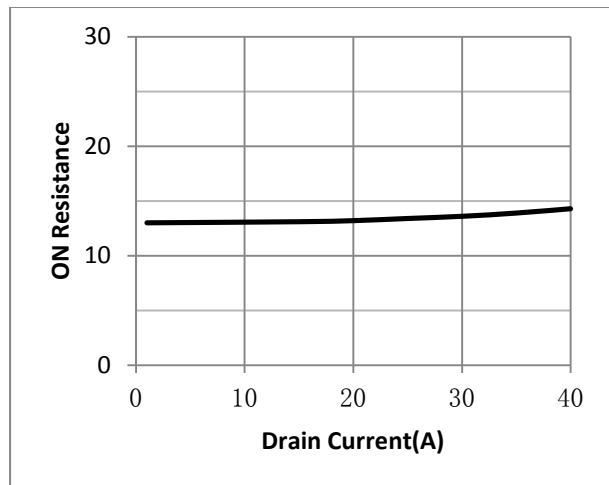


Fig.5 On-Resistance VS Gate Source Voltage

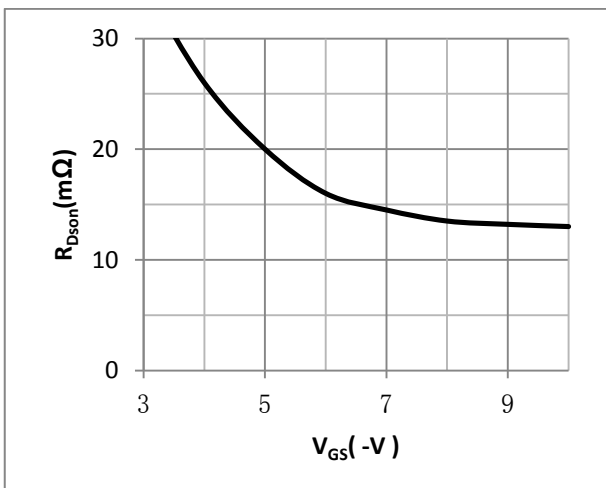


Fig.6 On-Resistance V.S Junction Temperature

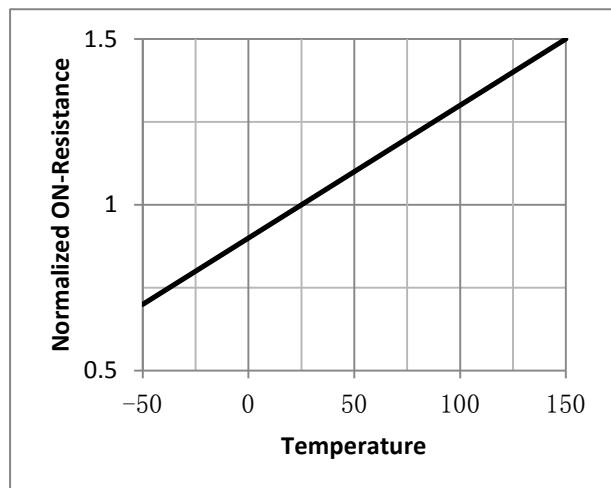


Fig.7 Switching Time Measurement Circuit

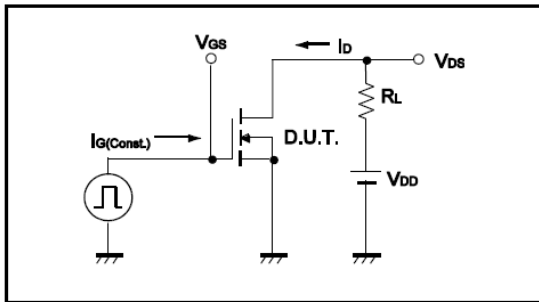


Fig.8 Gate Charge Waveform

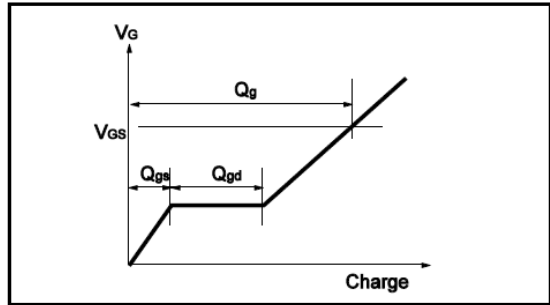


Fig.9 Switching Time Measurement Circuit

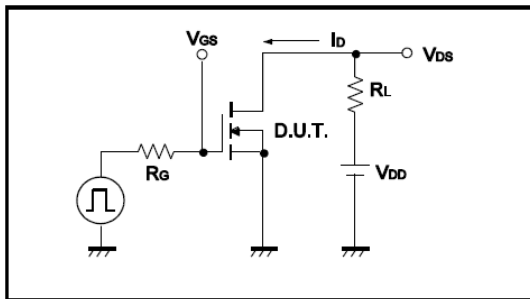


Fig.10 Gate Charge Waveform

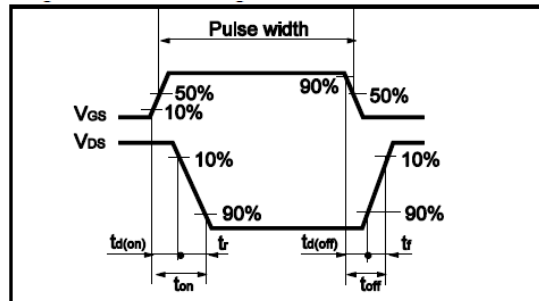


Fig.11 Avalanche Measurement Circuit

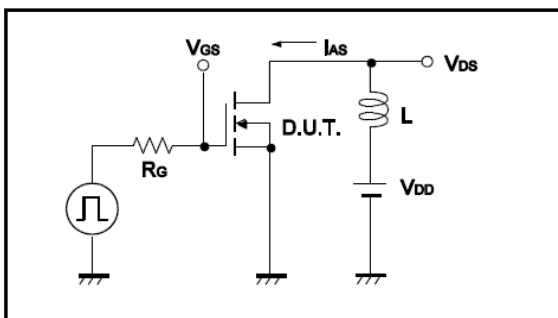
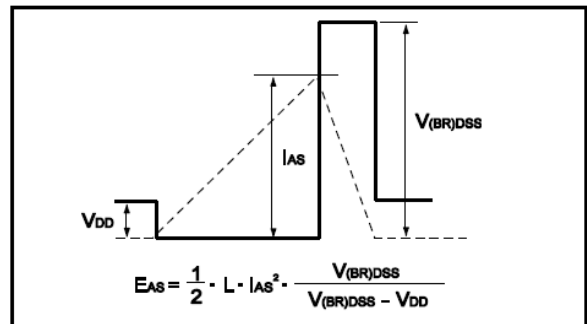
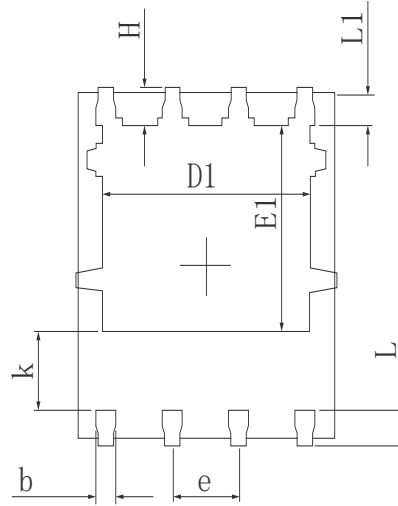
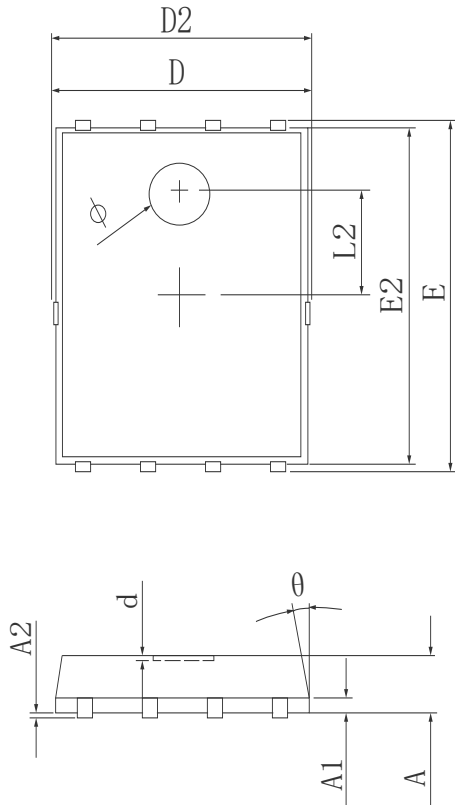
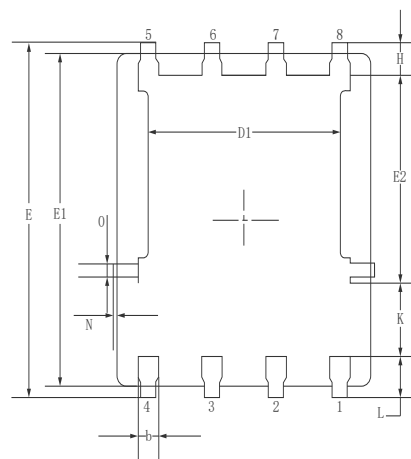
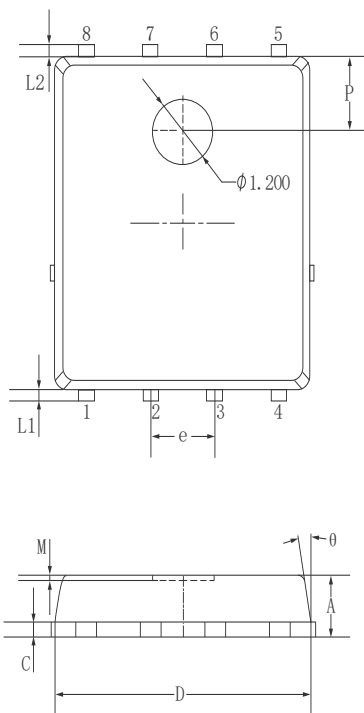


Fig.12 Avalanche Waveform



**•Dimensions (PDFN5\*6)**


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100

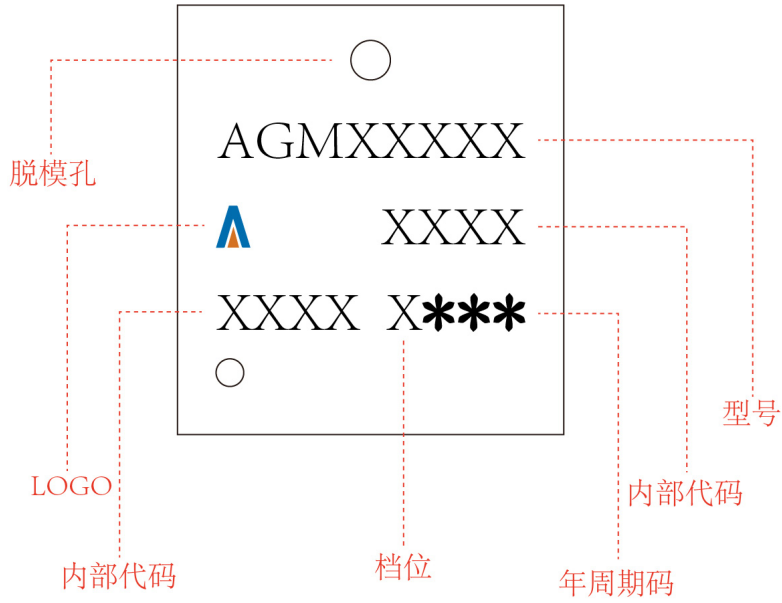


Symbol	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

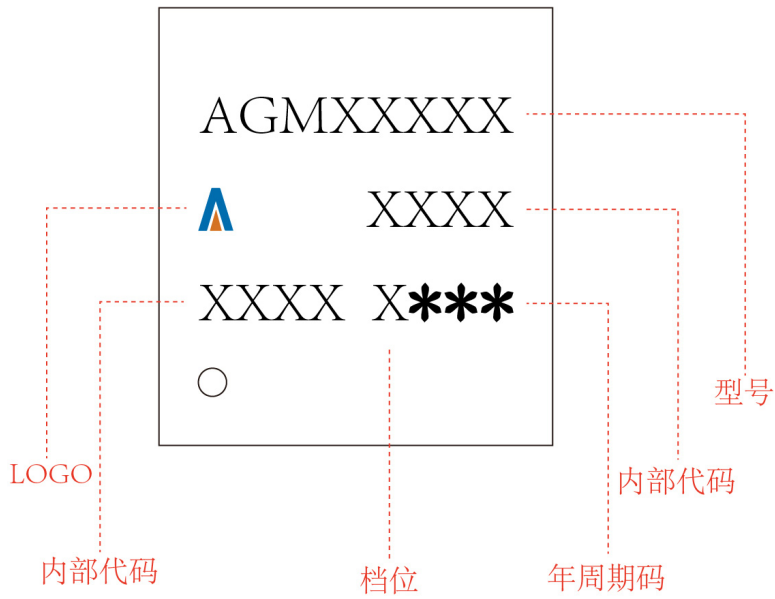
PDFN5\*6

Marking Instructions:

Model1:



Model2:




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